

## Annealing of Heavy Irradiated n-on-p Diodes at Temperatures 20°, 40°, 60° and 80°C

*Thursday 15 November 2012 11:10 (20 minutes)*

N-on-p Micron diodes were irradiated with reactor neutrons to  $1 \times 10^{15}$ ,  $2 \times 10^{15}$  and  $1 \times 10^{16}$  neq/cm<sup>2</sup>. Diodes were submitted to graduated annealing steps at 20°, 40°, 60° and 80°C to verify previously accepted accelerating annealing factors. The evolution of leakage currents and full depletion voltage (FDV) were measured. The FDV was determined from Capacity-Voltage curves and Charge Collection –Voltage curves from infrared laser beam.

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**Session Classification:** Detector Characterization and Simulations